



COMPLEMENTARY SILICON POWER TRANSISTORS

- STMicroelectronics PREFERRED SALESTYPES
- COMPLEMENTARY PNP - NPN DEVICES
- FULLY MOLDED ISOLATED PACKAGE
- 2000 V DC ISOLATION (U.L. COMPLIANT)

APPLICATIONS

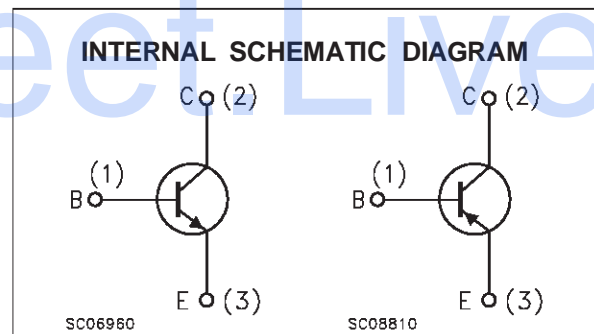
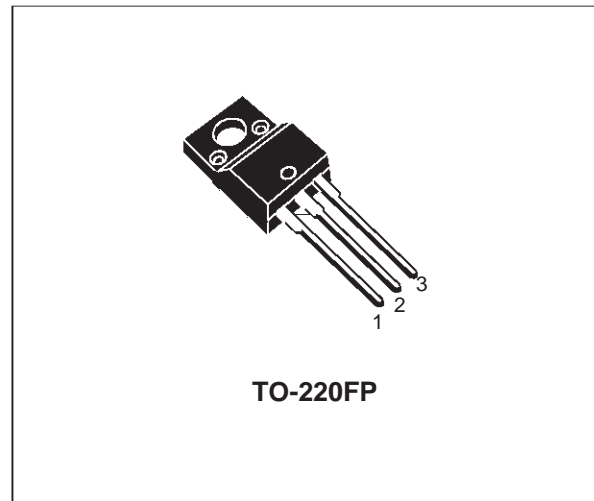
- GENERAL PURPOSE SWITCHING
- GENERAL PURPOSE AMPLIFIERS

DESCRIPTION

The BD241BFP is silicon epitaxial-base NPN transistors mounted in TO-220FP fully molded isolated package.

It is intended for power linear and switching applications.

The complementary PNP types is the BD242BFP.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		NPN	PNP	
V_{CER}	Collector-Base Voltage ($R_{BE} = 100 \Omega$)	BD241BFP		V
V_{CEO}	Collector-Emitter Voltage ($I_B = 0$)	BD242BFP		
V_{EBO}	Emitter-Base Voltage ($I_C = 0$)	BD241BFP		V
I_C	Collector Current	BD242BFP		A
I_{CM}	Collector Peak Current	BD241BFP		A
I_B	Base Current	BD242BFP		A
P_{tot}	Total Dissipation at $T_C \leq 25^\circ C$	BD241BFP		W
T_{stg}	Storage Temperature	BD242BFP		$^\circ C$
T_j	Max. Operating Junction Temperature	BD241BFP		$^\circ C$

For PNP types voltage and current values are negative.

BD241BFP / BD242BFP

THERMAL DATA

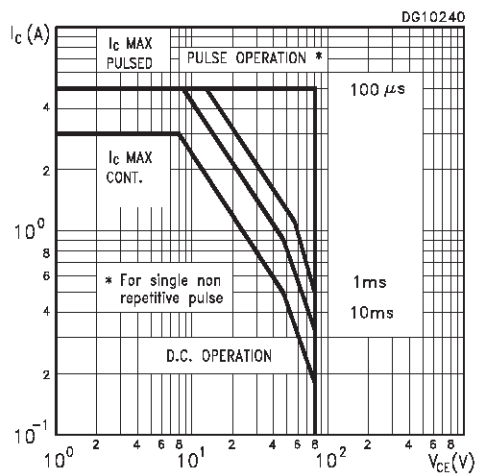
R _{thj-case}	Thermal Resistance Junction-case	Max	5.3	°C/W
-----------------------	----------------------------------	-----	-----	------

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I _{CEO}	Collector Cut-off Current (I _B = 0)	V _{CE} = 60 V			0.3	mA
I _{CES}	Collector Cut-off Current (V _{BE} = 0)	V _{CE} = 80 V			0.2	mA
I _{EBO}	Emitter Cut-off Current (I _C = 0)	V _{EB} = 5 V			1	mA
V _{CEO(sus)*}	Collector-Emitter Sustaining Voltage (I _B = 0)	I _C = 30 mA	80			V
V _{CE(sat)*}	Collector-Emitter Saturation Voltage	I _C = 3 A I _B = 0.6 A			1.2	V
V _{BE(ON)*}	Base-Emitter Voltage	I _C = 3 A V _{CE} = 4 V			1.8	V
h _{FE*}	DC Current Gain	I _C = 1 A V _{CE} = 4 V I _C = 3 A V _{CE} = 4 V	25 10			

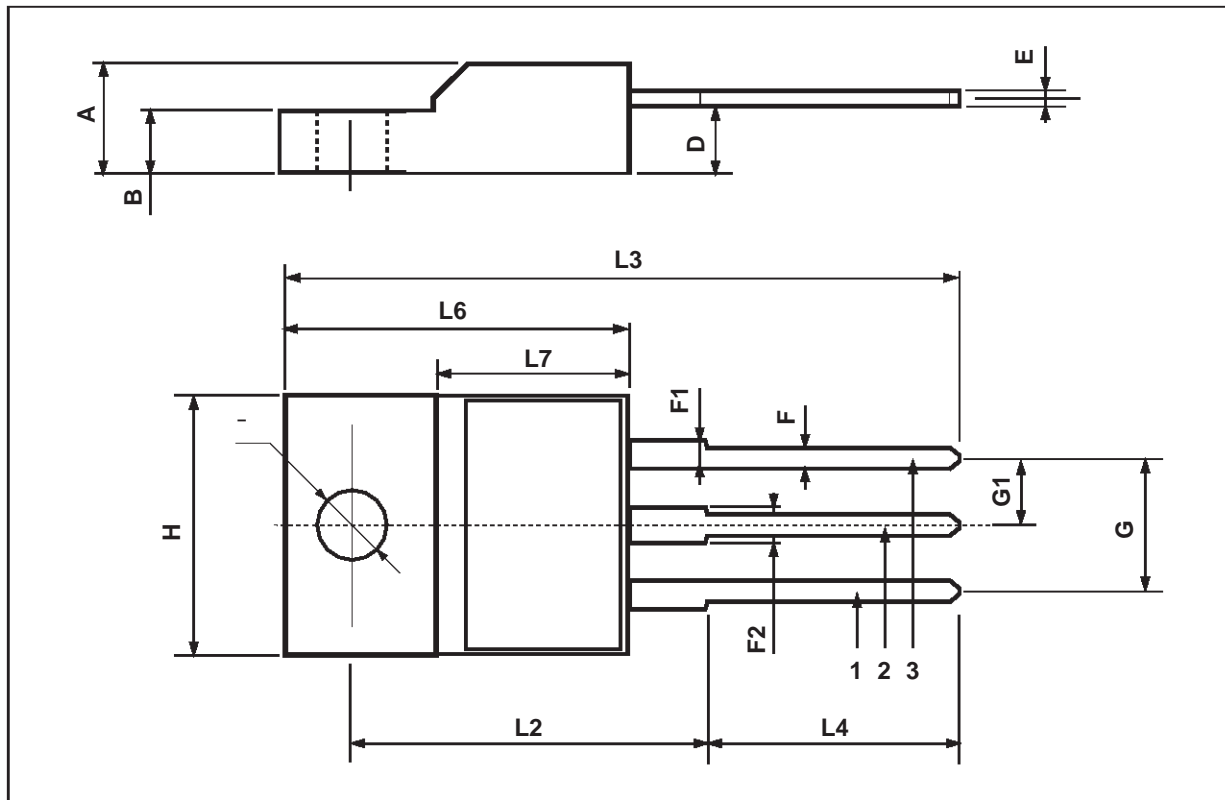
* Pulsed: Pulse duration = 300 μs, duty cycle ≤ 2 %
For PNP types voltage and current values are negative.

Safe Operating Area



TO-220FP MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	0.385		0.417
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126



Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specification mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is a trademark of STMicroelectronics

© 2001 STMicroelectronics – Printed in Italy – All Rights Reserved

STMicroelectronics GROUP OF COMPANIES

Australia - Brazil - China - Finland - France - Germany - Hong Kong - India - Italy - Japan - Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - U.S.A.

<http://www.st.com>